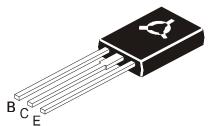


NPN SILICON POWER TRANSISTOR



CD13003D

TO126 Plastic Package

With Built - in Integrated Diode between Emitter & Collector

ABSOLUTE MAXIMUM RATINGS

DESCRIPTION	SYMBOL	VALUE	UNIT
Collector Base Voltage	V _{CBO}	600	V
Collector Emitter (sus) Voltage	V _{CEO}	400	V
Emitter Base Voltage	V _{EBO}	9.0	V
Collector Current Continuous	Ι _C	1.5	A
Peak (1)	I _{CM}	3.0	A
Base Current Continuous	Ι _Β	0.75	A
Peak (1)	I _{BM}	1.5	A
Emitter Current Continuous	Ι _Ε	2.25	A
Peak (1)	I _{EM}	4.5	А
Power Dissipation @ T _a =25 °C	PD	1.4	W
Derate Above 25ºC		11.2	mW/ ºC
Power Dissipation @ T _c =25 ºC	P _D	45	W
Derate Above 25ºC		360	mW/ ⁰C
Operating And Storage Junction Temperature Range	T _j , T _{stg}	- 65 to+150	°C

THERMAL RESISTANCE

Junction to Case	R _{th (j-c)}	2.77	°C/W
Junction to Ambient	R _{th (j-a)}	89	°C/W
Maximum Lead Temperature for Soldering	T.	275	°C
Purpose: 1/8" from Case for 5 Seconds	۰L	215	U

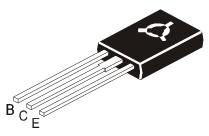
(1) Pulse Test: Pulse Width=5ms, Duty Cycle=10%

ELECTRICAL CHARACTERISTICS (T_a=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Collector Base Voltage	V _{CBO}	I _C =1mA, I _E =0	600			V
Collector Emitter (sus) Voltage	*V _{CEO(sus)}	I _C =10mA, I _B =0	400			V
Collector Cut Off Current	I _{CBO}	V _{CB} =600V, I _E =0			1.0	mA
		V _{CB} =600V, I _E =0, T _c =100°C			5.0	mA
Emitter Cut Off Current	I _{EBO}	V _{EB} =9V, I _C =0			1.0	mA

*Pulse Test: PW=300m6, Duty Cycle=2%

NPN SILICON POWER TRANSISTOR



TO126 Plastic Package

ELECTRICAL CHARACTERISTICS (T_a=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
DC Current Gain	*h _{FE}	**I _C =0.5A, V _{CE} =5V	11		30	
		I _C =1A, V _{CE} =5V	5		25	
Collector Emitter Saturation Voltage	*V _{CE (sat)}	I _C =0.5A, I _B =0.1A			0.5	V
		I _C =1A, I _B =0.25A			1.0	V
		I _C =1.5A, I _B =0.5A			2.5	V
		I _C =1A, I _B =0.25A,T _c =100°C			1.0	V
Base Emitter Saturation Voltage	*V _{BE (sat)}	I _C =0.5A, I _B =0.1A			1.0	V
		I _C =1A, I _B =0.25A			1.2	V
		I _C =1A, I _B =0.25A,T _c =100°C			1.1	V
Integrated Diode Forward Voltage	V _{FEC}	I _F =1A			2.0	V

DYNAMIC CHARACTERISTICS

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Current Gain Bandwidth Product	f _T	I _C =100mA, V _{CE} =10V, f=1MHz	4.0			MHz
Output Capacitance	C _{ob}	V_{CB} =10V, f=0.1MHz		21		pF

SWITCHING TIME

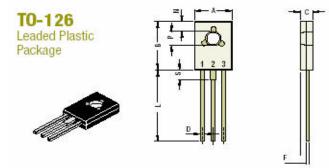
Turn On Time	t _{on}			1.1	μs
Storage Time	t _{stg}	V _{CC} =125V, I _C =1A, I _{B1} =0.2A, I _{B2} =0.2A	2.0	4.0	μs
Fall Time	t _r	'B2-0.27 (0.7	μs

Note:- Product is pre selected in DC current	Α	В	С	Е	F
gain (Groups A to F). CDIL reserves the right to ship any of the groups according to production availability.	11-16	15-19	18-22	21-25	24-30
MARKING	CD 13003DA XY	CD 13003DB XY	CD 13003D0 XY	CE C 1300 XY	
X = Year of Manufacturer Code Y = Month Code					

*Pulse Test:- PW=300ms, Duty Cycle=2%

TO126 Plastic Package

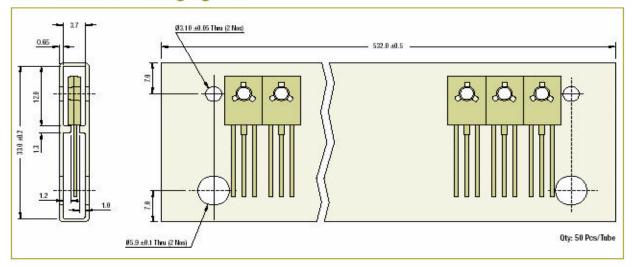
TO-126 (SOT-32) Plastic Package



DIM	Min	Max	DIM	Min	Max
A	7.12	8.38	G	4.07	5.08
В	10.16	11.43	L	15.00	16.63
С	2.29	3.04	M	0.89	1.65
D	0.64	0.88	N	3.31	4.44
E	2.040	2.285	Р	2.54	3.30
F	0.39	0.63	S	-	2.54

Pin Configurations Pin 1: Base Pin 2: Collector Pin 3: Emitter

TO-126 Series Packaging Tube



Packaging Specifications 1 & A: Tape and Armo Pads; T & R: Tape and Real: Bulk: Loose in Foly Bacs; Tuble: Tuble and Carton; K: 1,000											
Package / Case Type	Packaging Type	Std. Packing	ube and canon; i	Inner Carton			Outer Carton				
		Qty	Qts	Size L x W x H	Gross Wright	City	SizeLxWxH	Gross Weight			
				(cm)	(Kg)		(cm)	(Kg)			
TO-126	Bilk	2,000	2K	19x19x8	1.4	20K	46 x 38 x 22	15.6			
	Tube	1,000 (50 pcstube)	1K	55 x I x 10	1.5	10K	55 x 35 x 27	16.3			

TO126 Plastic Package

Component Disposal Instructions

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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